

IN THE CLAIMS:

Claims 1-8. (Cancelled)

9. (New) A photomask set comprising:
a first photomask in which a first intended pattern and a first alignment mark are defined; and
a second photomask in which a second intended pattern to overlay with the first intended pattern is defined,
wherein the second intended pattern and the first alignment mark have a substantially same line width.

10. (New) The photomask set of Claim 9, wherein the first photomask further comprises a second alignment mark having a substantially same line width as the first intended pattern.

11. (New) The photomask set of Claim 9, wherein the first alignment mark has the smallest size of the second intended pattern.

12. (New) A photomask set comprising:
a first photomask in which a first intended pattern and a first alignment mark are defined; and
a second photomask in which a second intended pattern to overlay with the first intended pattern and a second alignment mark are defined,
wherein the first intended pattern and the first alignment mark have a substantially same line width, and
the second intended pattern and the second alignment mark have a substantially same line width.

13. (New) The photomask set of Claim 12, wherein the first alignment mark has the smallest size of the first intended pattern and the second alignment mark has the smallest size of the second intended pattern.

14. (New) An alignment method comprising the steps of:
forming a first on-wafer intended pattern and an on-wafer alignment mark on a substrate by exposure using a first photomask in which a first intended pattern and an alignment mark are defined; and
overlaying a second intended pattern in a second photomask with the first on-wafer intended pattern,
wherein the second intended pattern in the second photomask has a substantially same line width as the alignment mark in the first photomask.
15. (New) The alignment method of Claim 14, wherein the line width of the alignment mark is equal to the smallest size of the line width of the second intended pattern in the second photomask.
16. (New) An alignment method comprising the steps of:
forming a first on-wafer intended pattern, a first on-wafer alignment mark, and a second on-wafer alignment mark on a substrate by exposure using a first photomask in which a first intended pattern, a first alignment mark, and a second alignment mark are defined;
calculating a correction value from a positional relationship between the first on-wafer alignment mark and the second on-wafer alignment mark formed on the substrate; and
correcting differences of overlay by the correction value in overlaying a second intended pattern in a second photomask with the first on-wafer intended pattern,
wherein the first intended pattern in the first photomask has a substantially same line width as the first alignment mark in the first photomask, and
the second intended pattern in the second photomask has a substantially same line width as the second alignment mark in the first photomask.
17. (New) The alignment method of Claim 16, wherein the line width of the second alignment mark is equal to the smallest size of the line width of the second intended pattern in the second photomask.

18. (New) An alignment method comprising the steps of:

forming a first on-wafer intended pattern and a first on-wafer alignment mark by exposure using a first photomask in which the first intended pattern and the first alignment mark are defined; and

overlaying the second intended pattern in the second photomask with the first on-wafer intended pattern by using a second photomask in which a second intended pattern and an second alignment mark are defined,

wherein the first intended pattern in the first photomask has a substantially same line width as the first alignment mark in the first photomask, and

the second intended pattern in the second photomask has a substantially same line width as the second alignment mark in the second photomask.

19. (New) The alignment method of Claim 18, wherein the line width of the second alignment mark is equal to the smallest size of the line width of the second intended pattern in the second photomask.